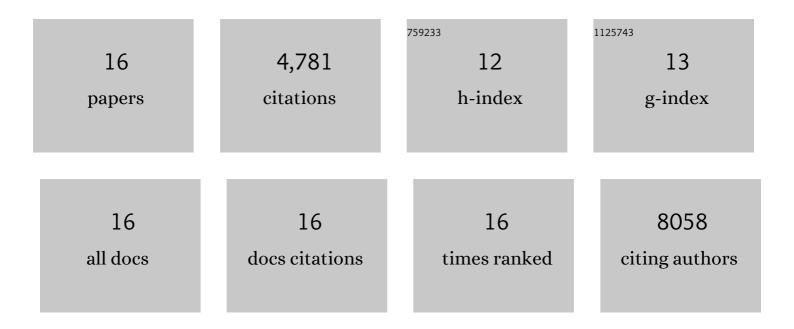


List of Publications by Year in descending order

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Τιτι Υιτ

#	Article	IF	CITATIONS
1	Heterogeneous Integration of 2D Materials and Devices on a Si Platform. , 2019, , 43-84.		5
2	High-Risk Breast Lesions: A Machine Learning Model to Predict Pathologic Upgrade and Reduce Unnecessary Surgical Excision. Radiology, 2018, 286, 810-818.	7.3	123
3	Parallel Stitching of 2D Materials. Advanced Materials, 2016, 28, 2322-2329.	21.0	195
4	Design, Modeling, and Fabrication of Chemical Vapor Deposition Grown MoS ₂ Circuits with E-Mode FETs for Large-Area Electronics. Nano Letters, 2016, 16, 6349-6356.	9.1	142
5	High-Performance WSe ₂ Complementary Metal Oxide Semiconductor Technology and Integrated Circuits. Nano Letters, 2015, 15, 4928-4934.	9.1	204
6	Origin and Control of OFF-State Leakage Current in GaN-on-Si Vertical Diodes. IEEE Transactions on Electron Devices, 2015, 62, 2155-2161.	3.0	185
7	MoS <inf>2</inf> FET fabrication and modeling for large-scale flexible electronics. , 2015, , .		3
8	Graphene/MoS ₂ Hybrid Technology for Large-Scale Two-Dimensional Electronics. Nano Letters, 2014, 14, 3055-3063.	9.1	554
9	Role of the Seeding Promoter in MoS ₂ Growth by Chemical Vapor Deposition. Nano Letters, 2014, 14, 464-472.	9.1	633
10	Dielectric Screening of Excitons and Trions in Single-Layer MoS ₂ . Nano Letters, 2014, 14, 5569-5576.	9.1	520
11	Synthesis and Transfer of Single-Layer Transition Metal Disulfides on Diverse Surfaces. Nano Letters, 2013, 13, 1852-1857.	9.1	612
12	Large-Area 2-D Electronics: Materials, Technology, and Devices. Proceedings of the IEEE, 2013, 101, 1638-1652.	21.3	46
13	Two-dimensional materials for ubiquitous electronics. , 2013, , .		1
14	Integrated Circuits Based on Bilayer MoS ₂ Transistors. Nano Letters, 2012, 12, 4674-4680.	9.1	1,526
15	Topological insulator nanostructures: Materials synthesis, Raman spectroscopy, and transport properties. Frontiers of Physics, 2012, 7, 208-217.	5.0	22
16	Negative rectification and negative differential resistance in nanoscale single-walled carbon nanotube p-n junctions. Theoretical Chemistry Accounts, 2011, 130, 353-359.	1.4	10